

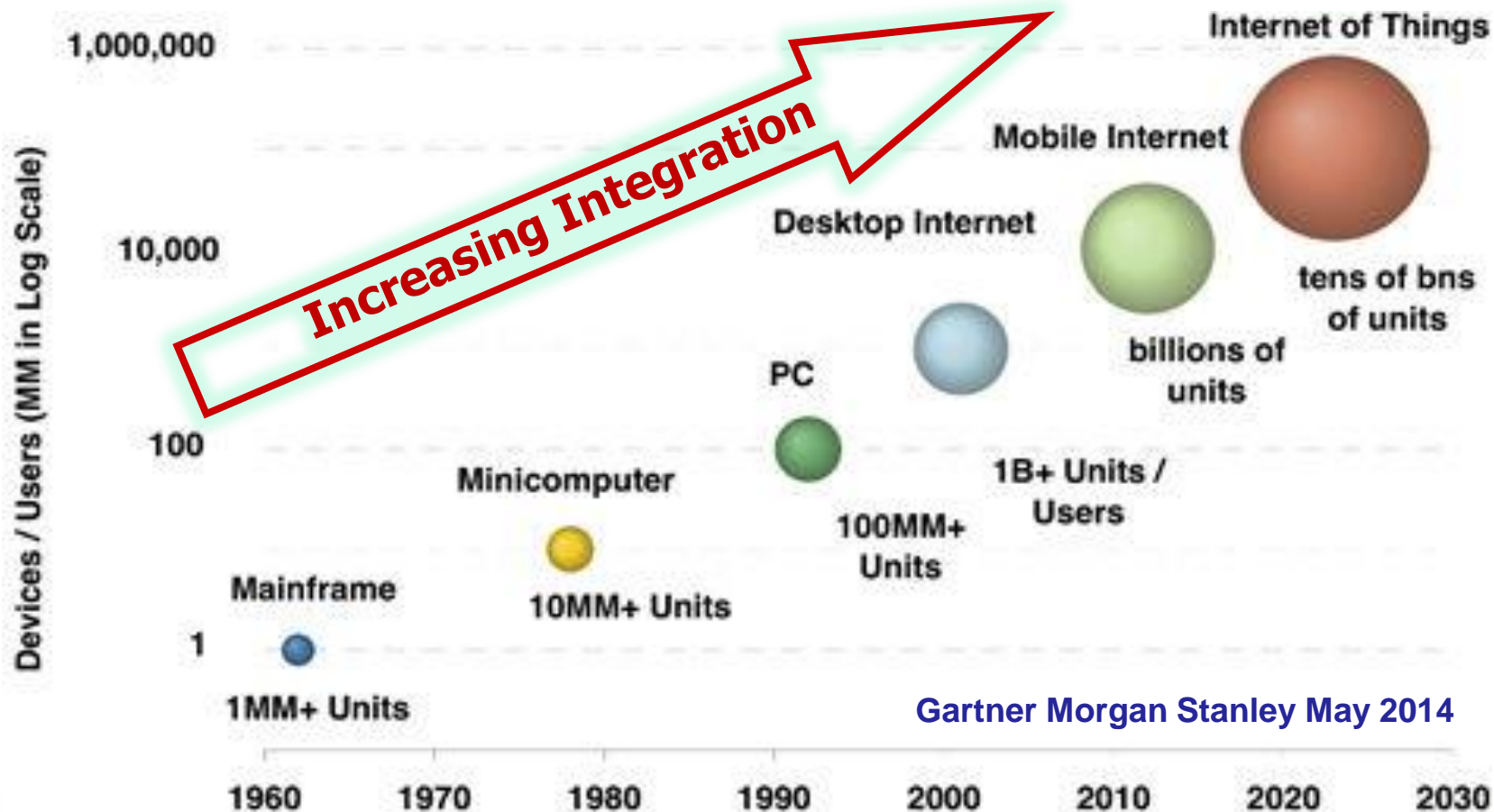
Wafer-Level-System-Integration (WLSI) Technologies for 2D and 3D System-in-Package

Douglas Yu, Ph.D.
TSMC R&D

Outline

- **Motivation-**
 - Industry trends
- **New SiP Technologies**
 - CoWoS Integration
 - Integrated Fan-Out WLP (InFO)
- **Conclusions and Outlook**

Trend and Motivation



Gartner Morgan Stanley May 2014

Semiconductor Product Revolutions

DT/NB PC



Smart Mobile



IoT/IoE



Fast, faster, faster

More Moore

High Performance

Cost, power, form-factor

More & More-than Moore

Optimized for User Exp'ce

Lower and smaller

More-than Moore

Wide-spectrum Systems

Semiconductor Market Trend

- **Smart Mobile and IoT/IoE**
 - System and modular devices
 - Lower cost, faster cycle-time and TTM
 - Light, thin, small, cool, green, fashionable
- **High Performance (Clouds)**
 - Power, memory bandwidth, data rate
 - Cost competitive
- **Moore's Law Challenges**
 - More challenging to maintain scaling factor (density) and cost against schedule.
 - Good SiP technologies create values and reduce Moore's Law pressure.

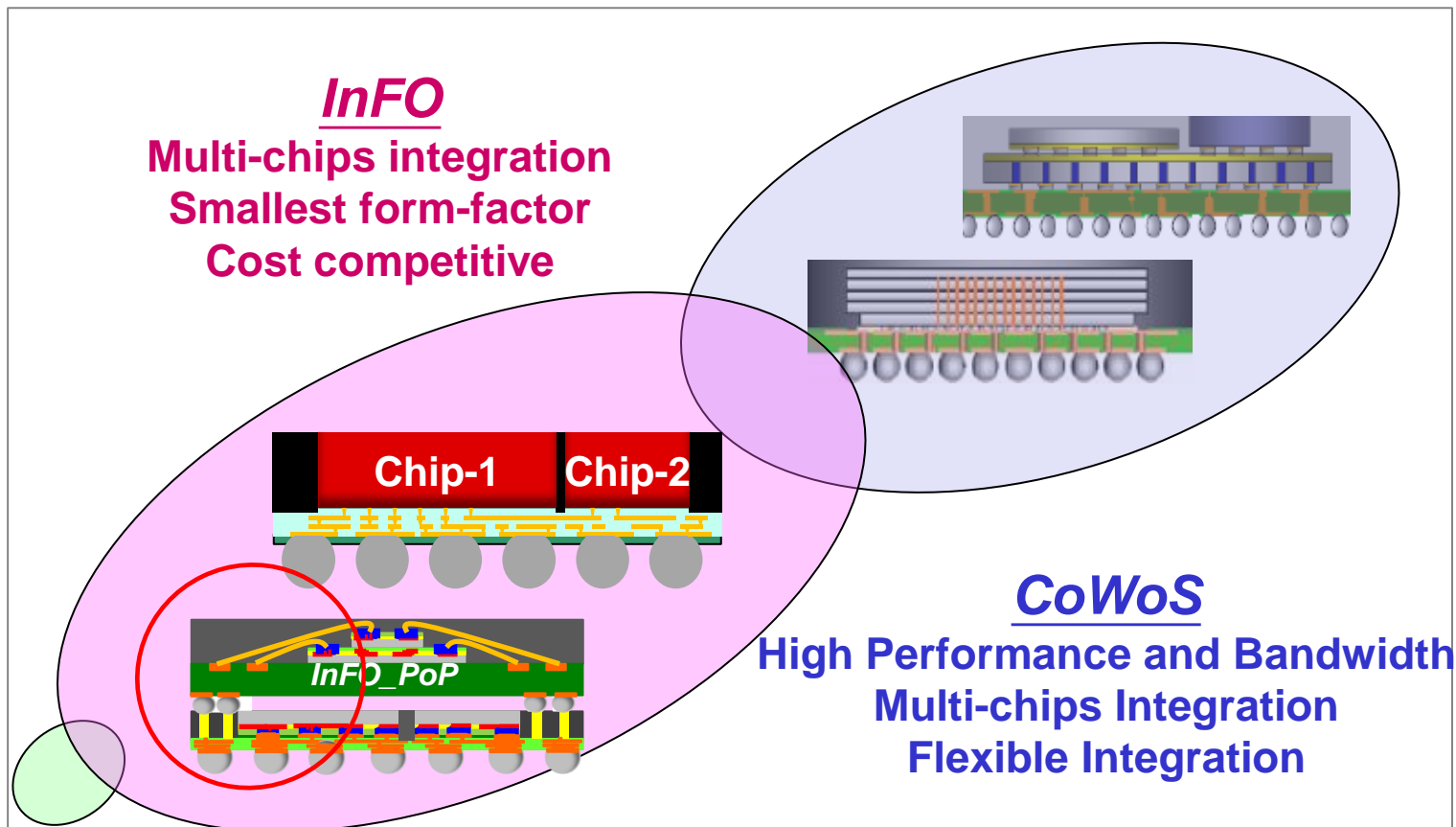
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TSMC WLSI Technologies

Full spectrum applications

I/O to Substrate and/or PCB



Die/PKG size (mm²)

WLCSP

TSV (3D-IC) & TIV (InFO_PoP)

TSMC WLSI Technologies

● WLSI Technologies

- Innovative Adv. PKG technologies in “wafer form”
- Leverage TSMC core competence and Grand Alliance
- Full spectrum- 2D→3D, Mobile→HP, and Today→NBTs.

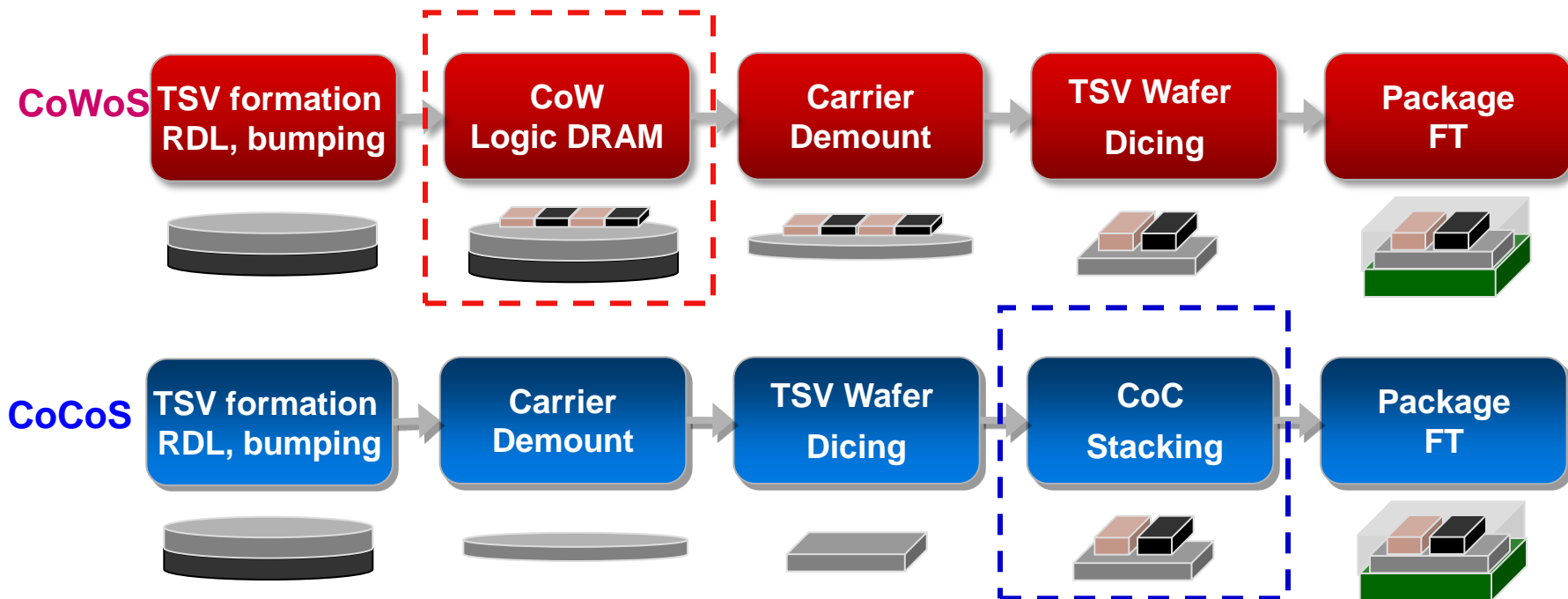
● Enable Chip-Partition

- Sustain Moore’s Law longer. Re-use technology/capacity and Design/IP (Adv./Mature, Analog/Digital, Logic/DRAM...)
- Built-in high-Q inductor on both Fan-In and Fan-Out WLP with chip cost savings. Enable Active/passive partition.

● *Powerful* and *Cool* Integration

- Integrate Chips (advanced, specialty) and PKGs
- PKG/Chip backside exposed, better thermal perform.
- Total Solution with single Design PDK, CT and TTM adv..

CoWoS™ Integration Flow

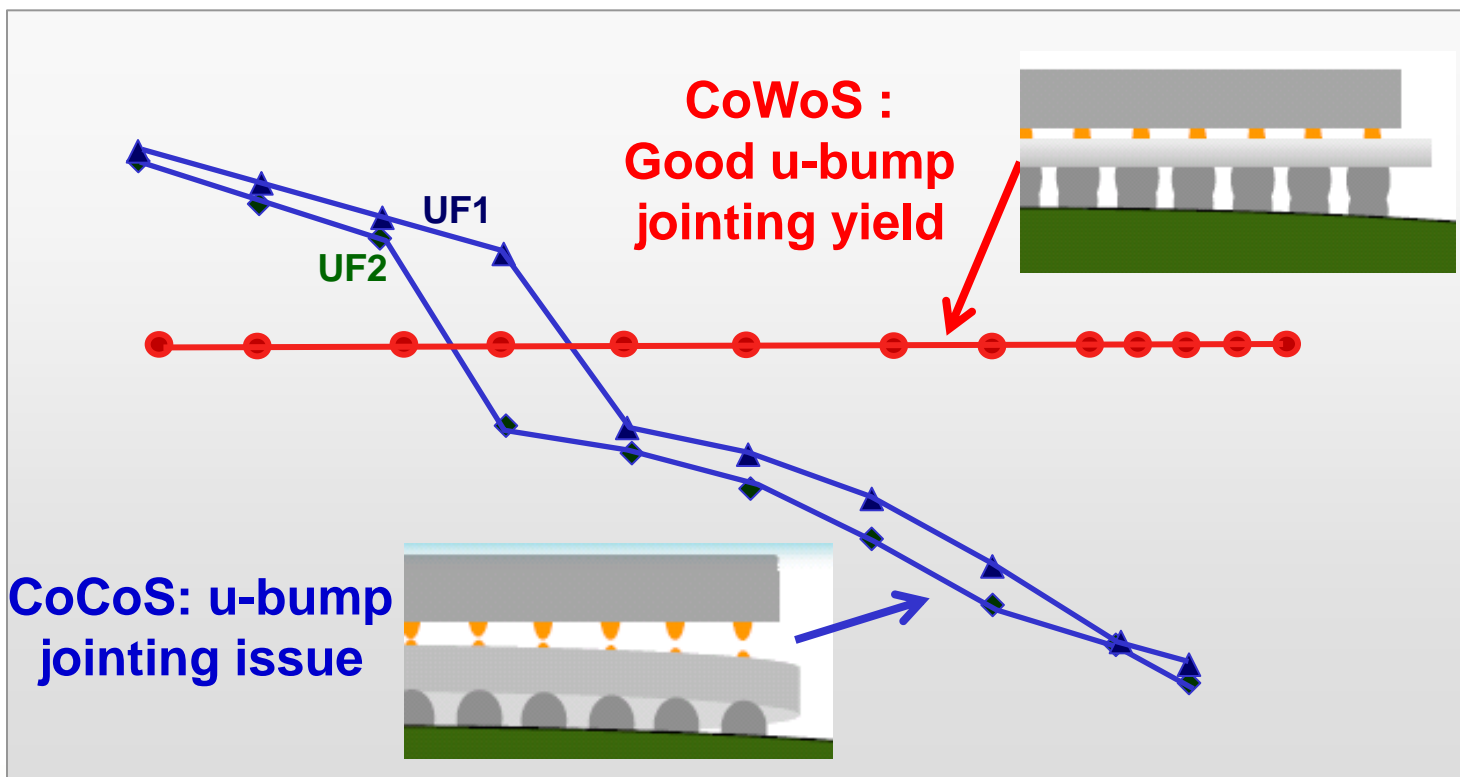


- CoWoS™ is a better integration and stacking flow on thin wafer/chips.
- Flexible integration of multi-chips for both Interposer and 3DIC.
- Low demanding substrate (embedded chips, cost, warpage control, and layers, etc) than other approaches, with yield and reliability advantages

CoWoS- Superior Warpage Control Enabling Excellent Yield

Thin 3D Die warpage > μ -bump height
 → Poor joint yield

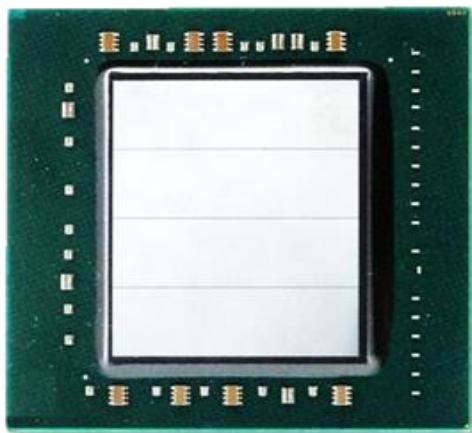
Max. Die-Level Warpage
 (μm) →



Temperature →

Commercialization of CoWoS™ Interposer Stacking

Courtesy of Xilinx



Homogeneous

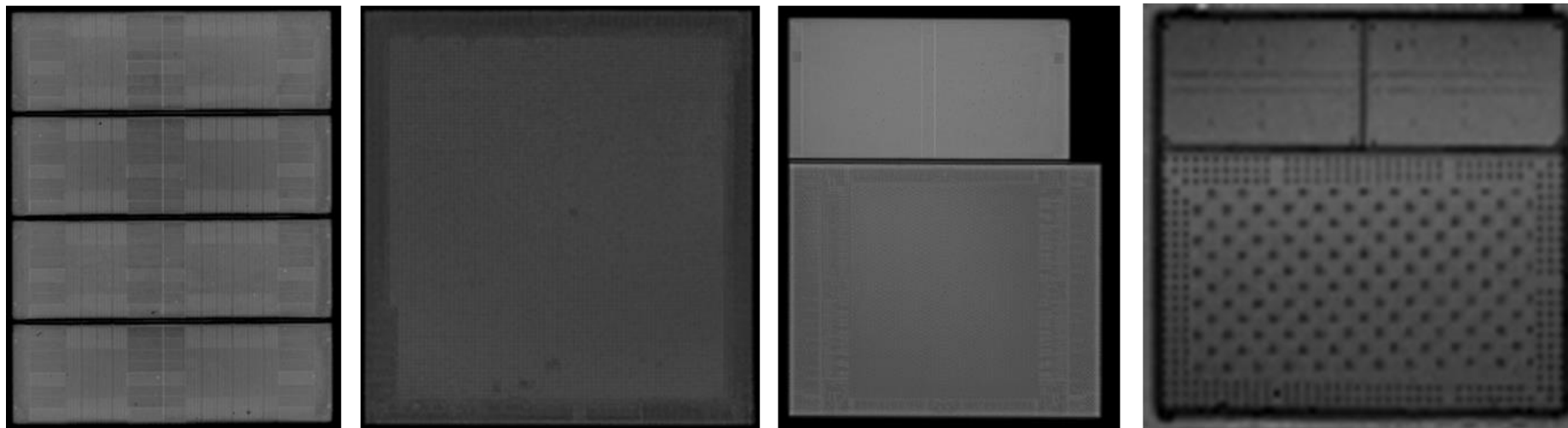
Courtesy of Xilinx



Heterogeneous

Both integrations use CoWoS™ integration flow.

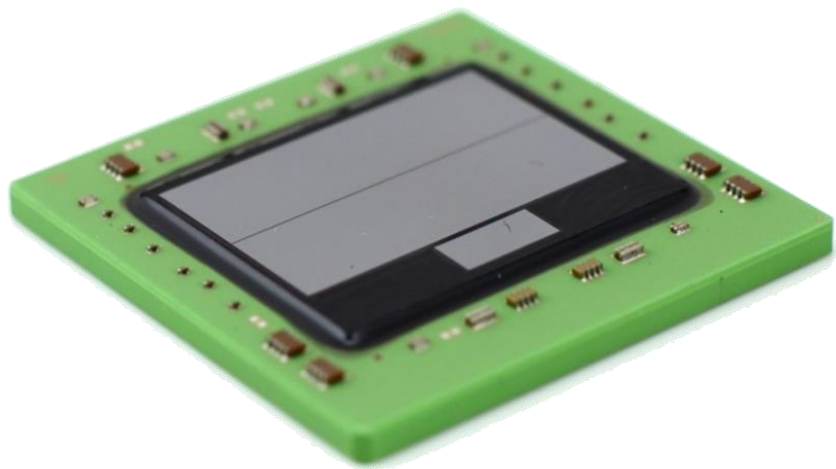
CoWoS™ Implementation of Flexible Multi-Chips Layouts



- High flexibility/efficiency chip layouts.
- Maximum integrity with **single piece Si** interposer and **single (μ)-bump pitch- yield and reliability advantages.**
- “**Single**” **assembly** (vs. multiple bridges / assemblies) on simplified substrate (vs. embedded substrate).

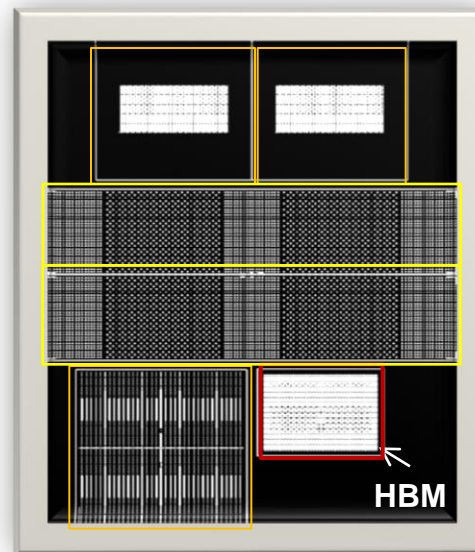
CoWoS™ Enable High Performance

- Chip-partition into same or different nodes with ultra-high interconnect density
- Integrate WIO or HBM with Logics, exceeding full reticle size.



(Pictures Courtesy of Xilinx)

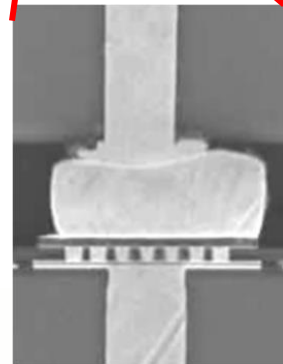
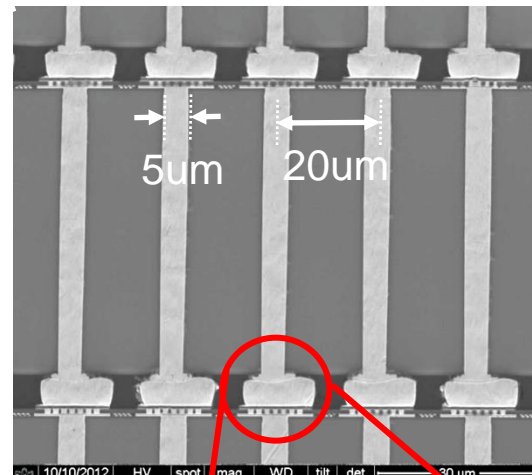
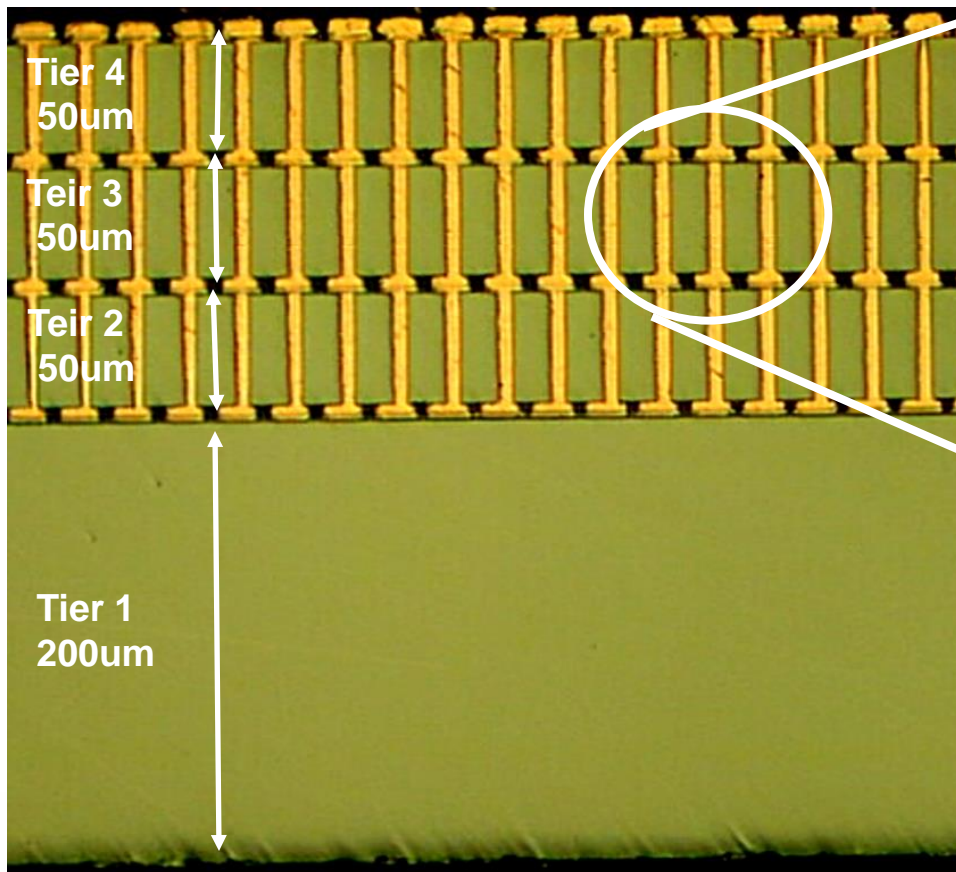
Floor Plan



HBM: High bandwidth memory

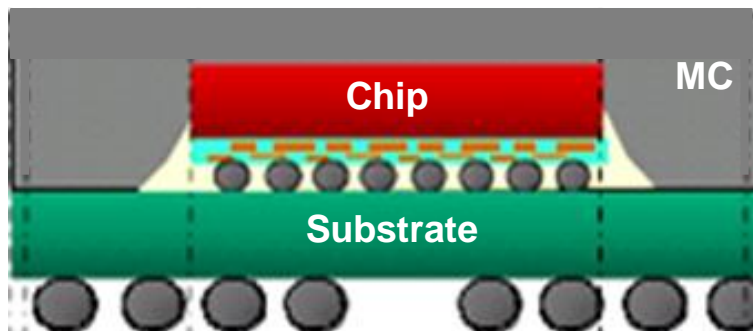
Multi-Tier TSV Scaling for 3D-IC

- Low-cost, high-density bond.
- Multi-tier stacking demonstrated.

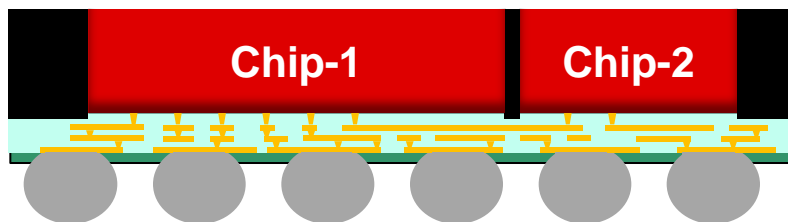


Values from Subtraction

Flip Chip



InFO-WLP



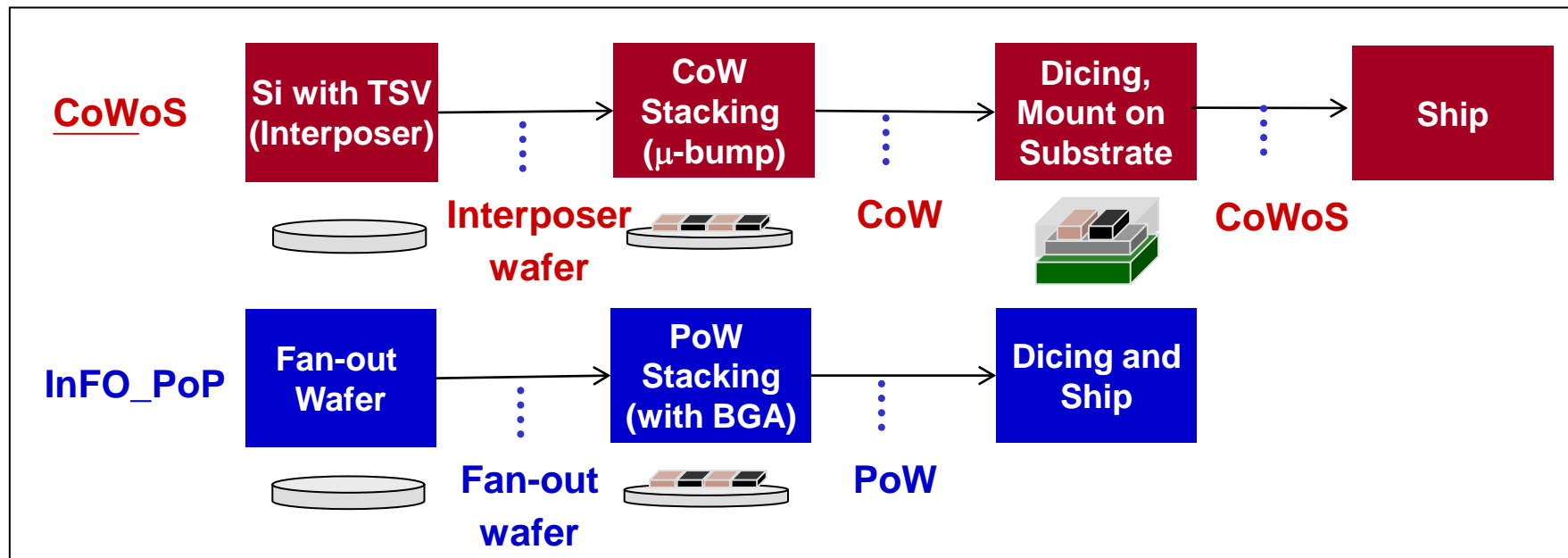
● Flip-Chip

- Substrate and bump add to total thickness and R_{th}
- Bumping and assembly cost

● Integrated Fan-Out WLP (InFO)

- Simplified architecture.
- Lower profile, cost and R_{th} .
- Powerful and Cool integration: single- and multi-chips, 2D/3D, Mobile/HP, Today/NBTs, and Logic/memory, Adv./Mature nodes Logics, etc.

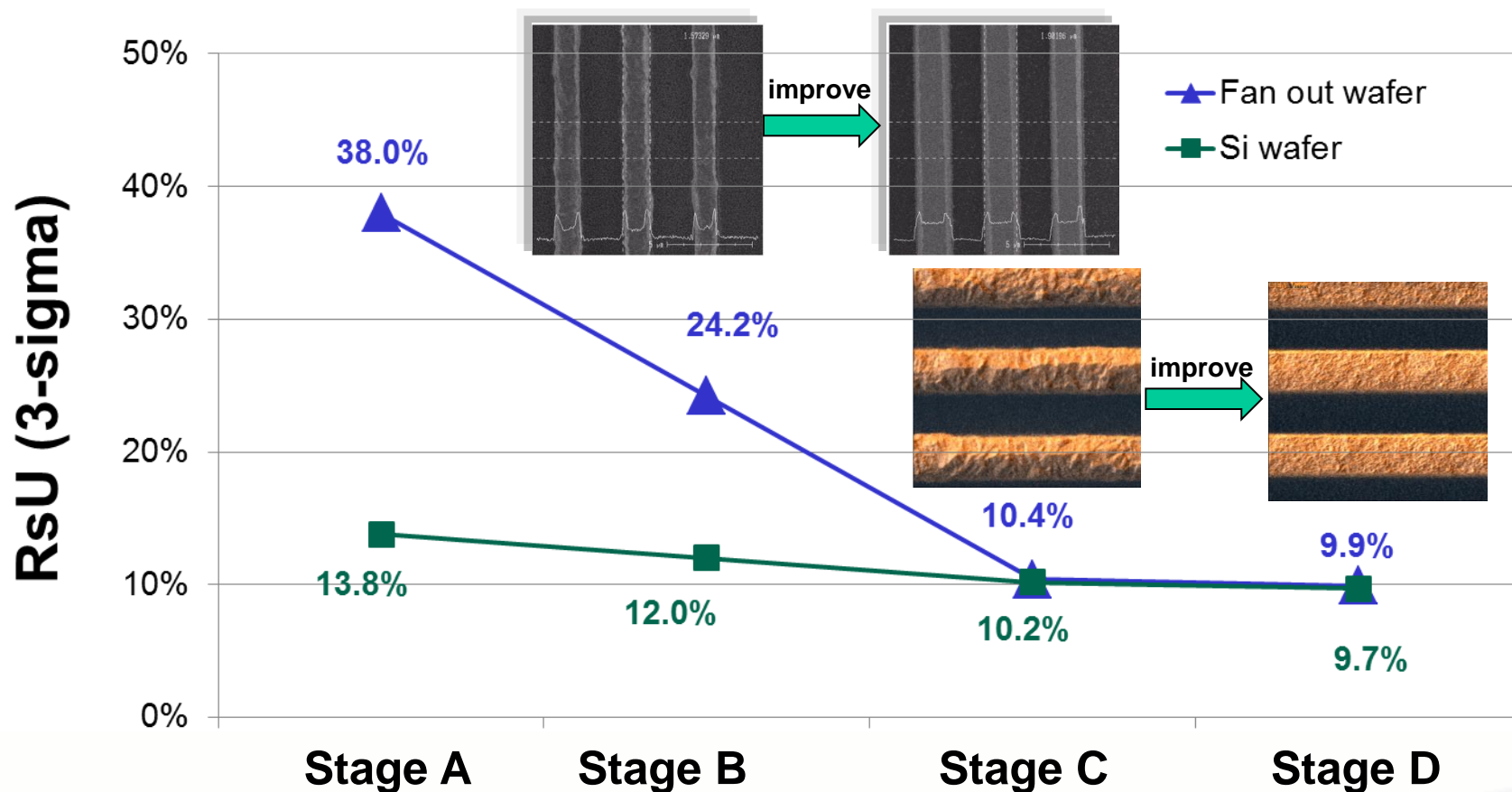
InFO_PoP Leverages CoWoS



- **CoWoS:** SoC Chips stack on TSV wafer.
- **InFO_PoP:** PoW (PKG-on-Wafer) DRAM PKG stack on InFO wafer.
 Key processes sharing: Thin wafer process, Carrier bond/de-bond, and RDL, etc.

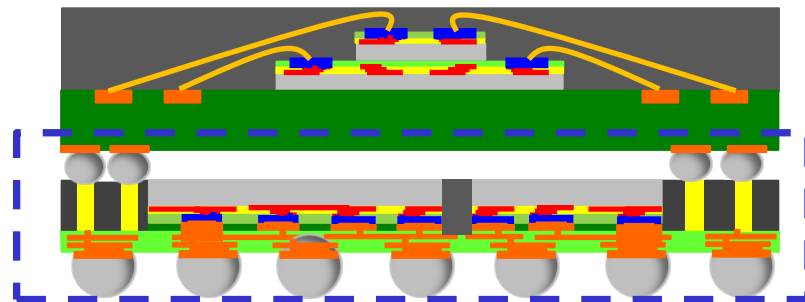
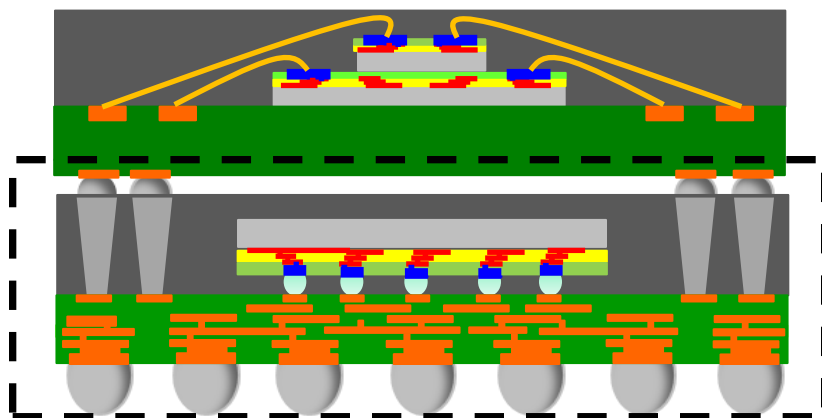
InFO RDL Tight Process Control

- **W/S=2/2 μ m**, Rs variation (RsU) $3\sigma \leq 10\%$



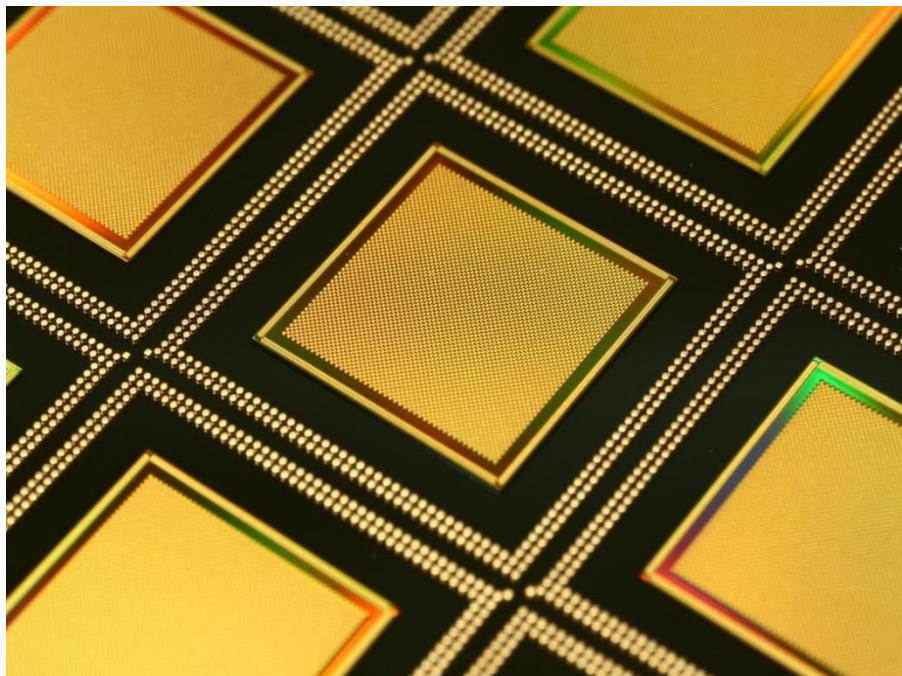
TSMC InFO_PoP for AP/DRAM System-Integration

- Integrated Fan-Out WLP (InFO) grows from 2D InFO to 3D InFO_PoP (MoL Stacking).
- Leadership in low profile, low power, high memory bandwidth with competitive cost

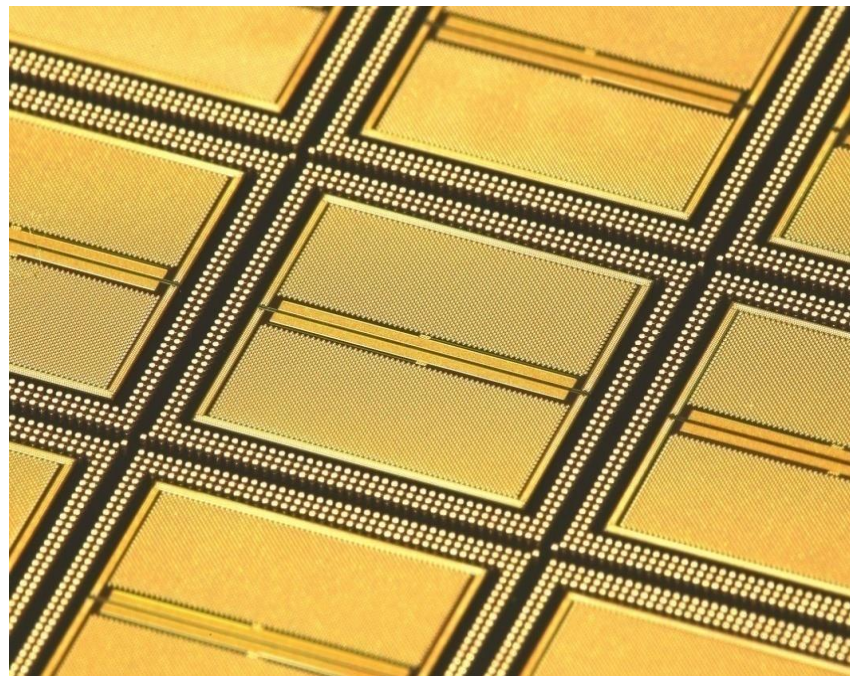


TSMC InFO_PoP with TIV - Top View

- Wafer form process, capable of very high density TIV Integration for high bandwidth.

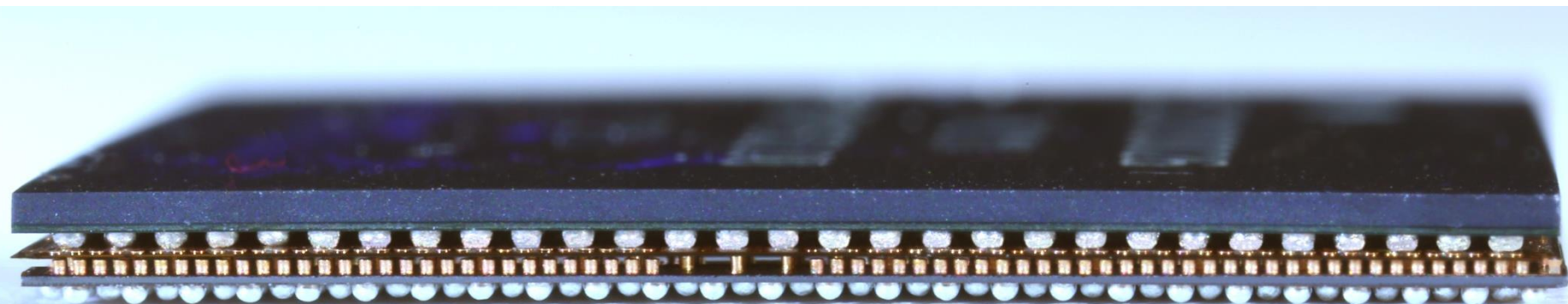


Single-Chip InFO_PoP

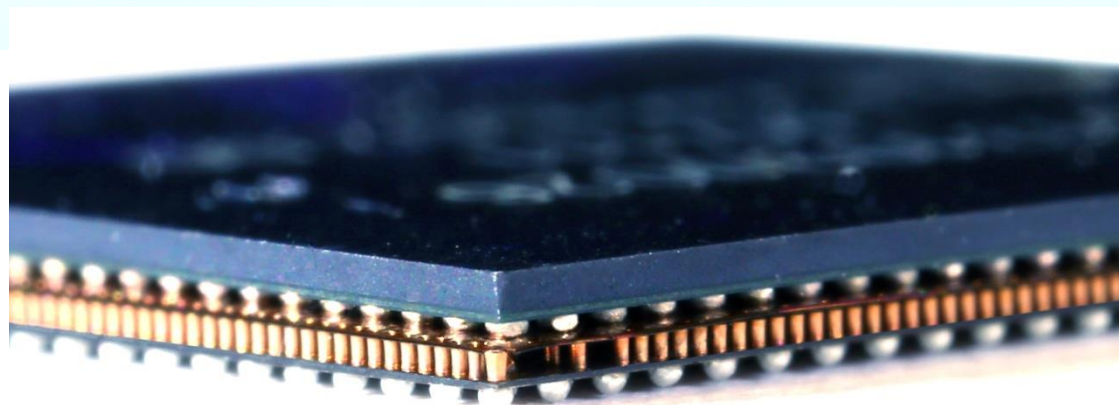


Dual-Chip InFO_PoP

TSMC InFO-PoP 3D-Stacking with DRAM PKG



DRAM →
InFO with TIV →

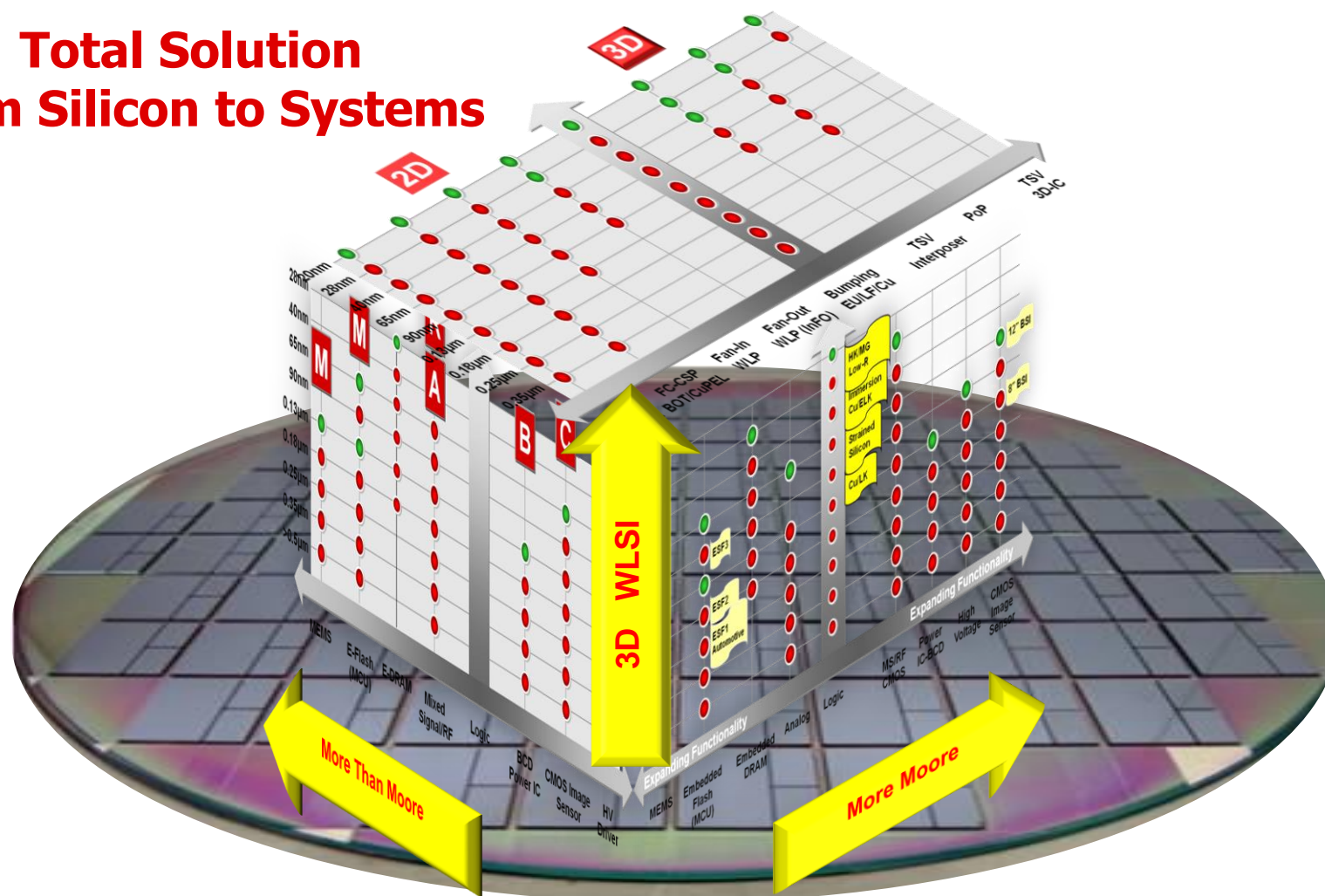


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Most Powerful System Integration

**Total Solution
 From Silicon to Systems**



**Wafer Level System Integration
 WLSI**

Summary

- TSMC WLSI Technologies developed for wide-range applications- 2D/3D, Mobile/HP, and Today/NBTs.
- Total Solution from **Silicon** to **System** with innovative, disruptive and cost-competitive Adv. PKG options. Paradigm shift from IC- to System-Foundry.
- Enable Chip-Partition, **Powerful** and **Cool** Integration. Sustain Moore's Law longer.